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NXP Semiconductors/Freescale Semiconductor, Inc. BTA312-800ET,127

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BTA312-800ET 3Q Hi-Com Triac

28 April 2015

Product data sheet

#### 1. **General description**

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package. This "series ET" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers including microcontrollers. It is used in applications where "high junction operating temperature" capability is required.

#### Features and benefits 2.

- 3Q technology for improved noise immunity •
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate •
- High junction operating temperature capability •
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only

#### **Applications** 3.

- Applications subject to high temperature
- Electronic thermostats (heating and cooling) •
- High power motor controls e.g. washing machines and vacuum cleaners •
- Refrigeration and air-conditioner compressor controls

#### Quick reference data 4.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \text{ Fig. 4}; \text{ Fig. 5}$	-	-	100	A
Tj	junction temperature		-	-	150	°C
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 125 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	12	A







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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			1		
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	-	10	mA

## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2
2	T2	main terminal 2	$2 \rightarrow 0 \leq 1$	sym051
3	G	gate		
mb	Τ2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

## 6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
BTA312-800ET	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78



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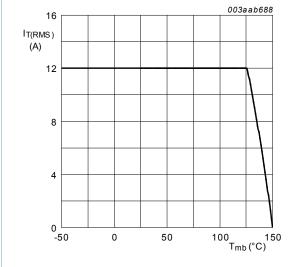
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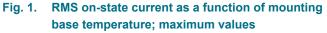
## 7. Limiting values

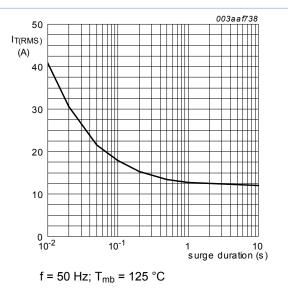
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Mir	n Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 125 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	12	A
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; <u>Fig. 4; Fig. 5</u>	-	100	A
		full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 16.7 \text{ ms}$	-	110	A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	50	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 20 mA	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	А
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	) 150	°C
Tj	junction temperature		-	150	°C









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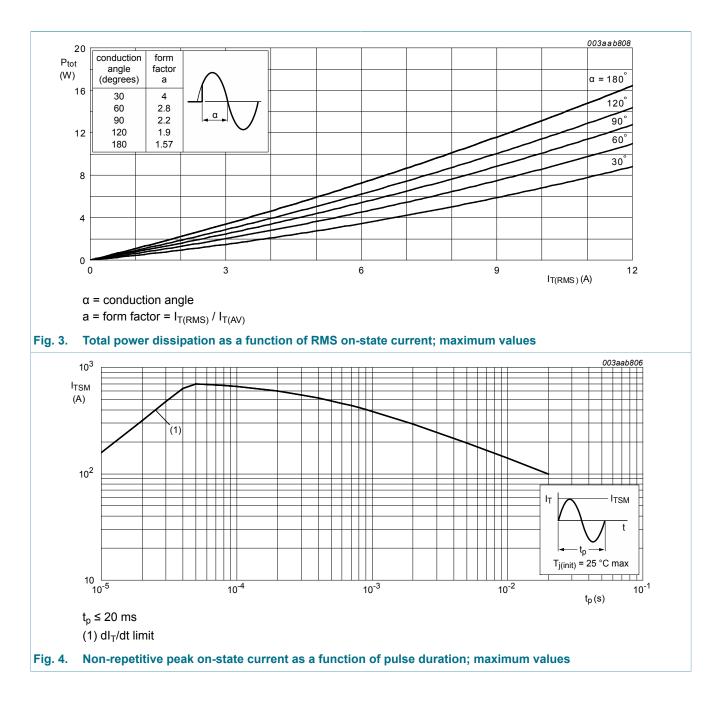
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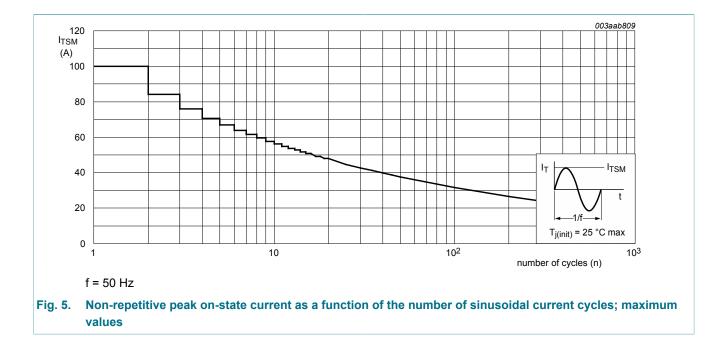




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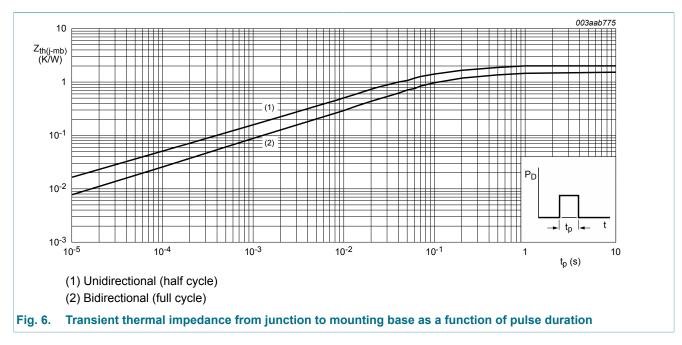
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## 8. Thermal characteristics

Table 5. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	1.5	K/W
		half cycle; Fig. 6	-	-	2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W



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## 9. Characteristics

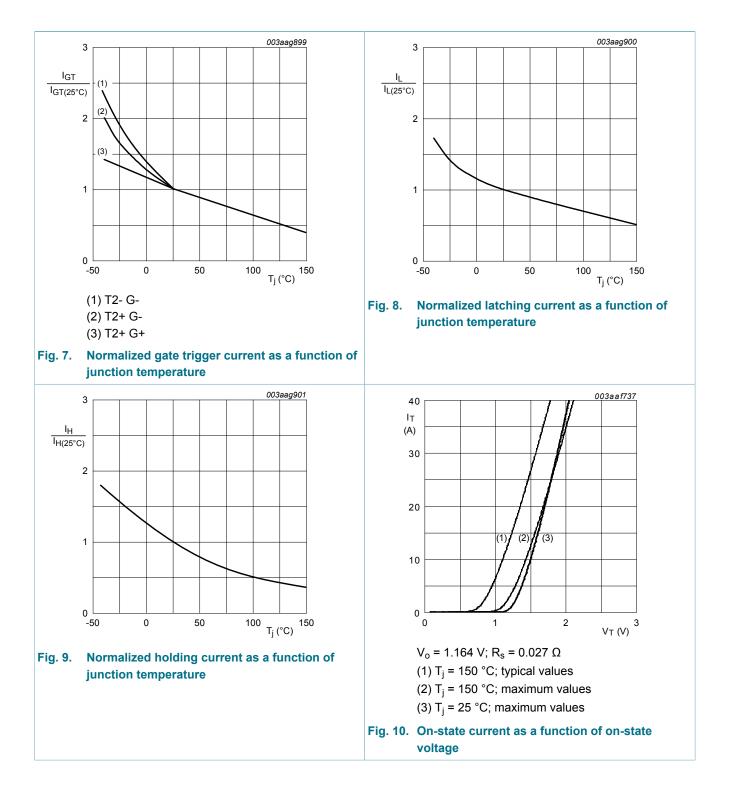
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D$ = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	-	10	mA
		$V_D$ = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	-	10	mA
IL	latching current	$V_D$ = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	25	mA
		$V_D$ = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	30	mA
		$V_D$ = 12 V; I <sub>G</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	25	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 11	-	0.8	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 150 °C; Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 150 °C	-	0.4	0.2	mA
Dynamic cl	naracteristics	· · · ·				
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; T <sub>j</sub> = 150 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	30	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_{D} = 400 \text{ V};  \text{T}_{\text{j}} = 150 \text{ °C};  \text{I}_{\text{T}(\text{RMS})} = 12 \text{ A}; \\ \text{dV}_{\text{com}}/\text{dt} = 20 \text{ V}/\mu\text{s}; \text{ (snubberless condition); gate open circuit}$	2	-	-	A/ms
		$V_{D} = 400 \text{ V};  \text{T}_{\text{j}} = 150 ^{\circ}\text{C};  \text{I}_{\text{T}(\text{RMS})} = 12 \text{ A};$ $dV_{\text{com}}/dt = 10 \text{ V}/\mu\text{s}; \text{ gate open circuit}$	3.5	-	-	A/ms
		$V_D$ = 400 V; T <sub>j</sub> = 150 °C; I <sub>T(RMS)</sub> = 12 A; dV <sub>com</sub> /dt = 1 V/µs; gate open circuit	5	-	-	A/ms



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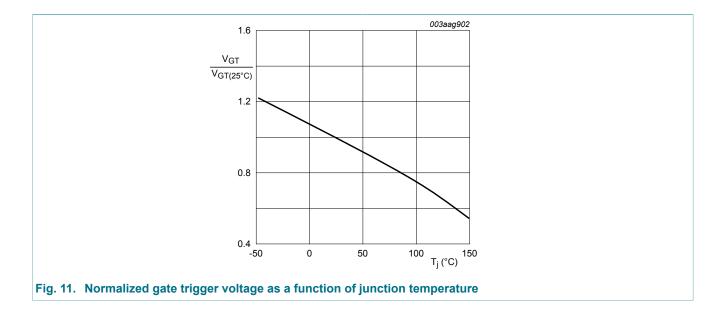




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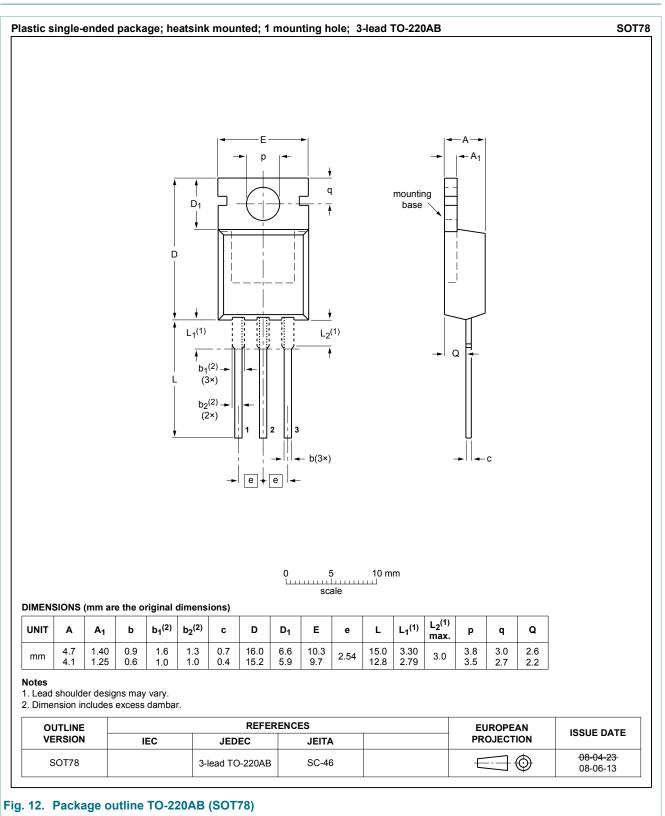


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## 10. Package outline



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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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